

HIGH-SPEED 4K x 8 FourPort[™] STATIC RAM

Features

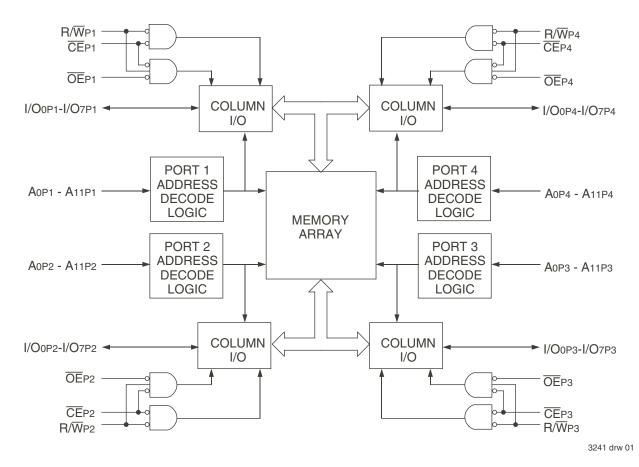
- High-speed access
 Commercial: 20ns (max.)
 - Low-power operation
- Low-power operation
 IDT7054L
 Active: 750mW (typ.)
 - Standby: 1.5mW (typ.)
- True FourPort memory cells which allow simultaneous access of the same memory locations
- Fully asynchronous operation from each of the four ports: P1, P2, P3, and P4
- TTL-compatible; single 5V (±10%) power supply
- Available in 128 pin Thin Quad Flatpack package

Description

The IDT7054 is a high-speed 4K x 8 FourPortTM Static RAM designed to be used in systems where multiple access into a common RAM is required. This FourPort Static RAM offers increased system performance in multiprocessor systems that have a need to communicate in real time and also offers added benefit for high-speed systems in which multiple access is required in the same cycle.

The IDT7054 is also designed to be used in systems where on-chip hardware port arbitration is not needed. This part lends itself to those systems which cannot tolerate wait states or are designed to be able to externally arbitrated or withstand contention when all ports simultaneously access the same FourPort RAM location.

The IDT7054 provides four independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for



Functional Block Diagram

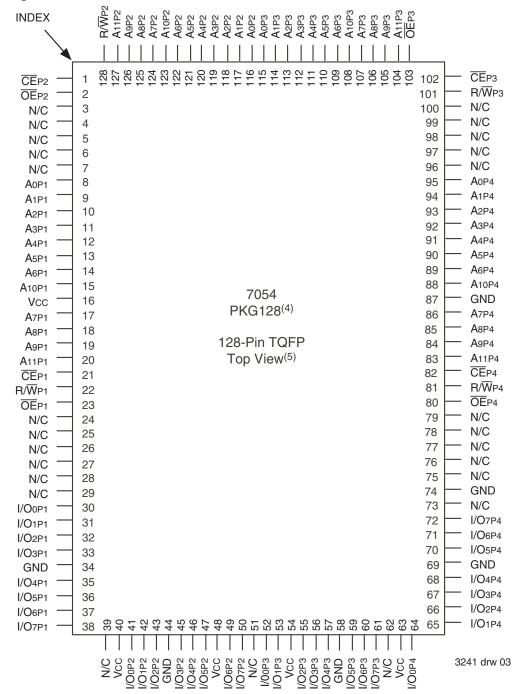
High-Speed 4K x 8 FourPort[™] Static RAM

reads or writes to any location in memory. It is the user's responsibility to ensure data integrity when simultaneously accessing the same memory location from all ports. An automatic power down feature, controlled by \overline{CE} , permits the on-chip circuitry of each port to enter a very low power standby power mode.

Fabricated using CMOS high-performance technology, this FourPort SRAM typically operates on only 750mW of power.

The IDT7054 is packaged in a 128-pin Thin Quad Flatpack (TQFP).

Pin Configuration^(1,2,3)



NOTES:

1. All Vcc pins must be connected to the power supply.

2. All GND pins must be connected to the ground supply

3. Package body is approximately 14mm x 20mm x 1.4mm

4. This package code is used to reference the package diagram.

5. This text does not indicate orientation of the actual part-marking.



High-Speed 4K x 8 FourPort™ Static RAM

Pin Configurations^(1,2)

Symbol	Pin Name			
A0 P1 - A11 P1	Address Lines - Port 1			
A0 P2 - A11 P2	Address Lines - Port 2			
A0 P3 - A11 P3	Address Lines - Port 3			
A0 P4 - A11 P4	Address Lines - Port 4			
I/O0 P1 - I/O7 P1	Data I/O - Port 1			
1/O0 P2 - 1/O7 P2	Data I/O - Port 2			
I/O0 P3 - I/O7 P3	Data I/O - Port 3			
1/O0 P4 - 1/O7 P4	Data I/O - Port 4			
R/₩ P1	Read/Write - Port 1			
R/W P2	Read/Write - Port 2			
R/₩ P3	Read/Write - Port 3			
R/₩ P4	Read/Write - Port 4			
GND	Ground			
CE P1	Chip Enable - Port 1			
CE P2	Chip Enable - Port 2			
CE P3	Chip Enable - Port 3			
CE P4	Chip Enable - Port 4			
OE P1	Output Enable - Port 1			
OE P2	Output Enable - Port 2			
OE P3	Output Enable - Port 3			
OE P4	Output Enable - Port 4			
Vcc	Power			

NOTES:

1. All Vcc pins must be connected to the power supply.

2. All GND pins must be connected to the ground supply.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit		
Vcc	Vcc Supply Voltage		5.0	5.5	V		
GND Ground		0	0	0	V		
Vн	Input High Voltage	2.2		6.0 ⁽²⁾	V		
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V		

NOTES:

1. V $\scriptstyle \mathbb{L} \geq$ -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

Commercial Temperature Range

Capacitance⁽¹⁾ (TA = +25°C, f = 1.0MHz) TQFP ONLY

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit			
Cin	Input Capacitance	VIN = 0V	9	pF			
Соит	Output Capacitance	Vout = 0V	10	pF			

NOTES:

1. This parameter is determined by device characterization but is not production tested.

 3dV references the interpolated capacitance when the input and the output signals switch from 0V to 3V or from 3V to 0V.

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Temperature	GND	Vcc
0°C to +70°C	0V	5.0V <u>+</u> 10%
-40°C to +85°C	0V	5.0V <u>+</u> 10%
	0°C to +70°C	0°C to +70°C 0V

NOTES:

3241 tbl 04

1. This is the parameter TA. This is the "instant on" case temperature.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit				
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V				
TBIAS	Temperature Under Bias	-55 to +125	°C				
Тѕтс	Storage Temperature	-65 to +150	°C				
Ιουτ	DC Output Current	50	mA				
324							

NOTES:

3241 tbl 01

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.



DC Electrical Characteristics Over the Operating Temperature and Supply Voltage $Range^{(1,5)}$ (Vcc = 5.0V ± 10%)

						4X20 I Only		1X25 & Ind		1X35 Only	
Symbol	Parameter	Condition	Versio	on	TYP. ⁽²⁾	Max.	TYP. ⁽²⁾	Max.	TYP. ⁽²⁾	Max.	Unit
ICC1	Operating Power Supply Current (All Ports Active)	oply Current Outputs Disabled	COM'L.	S L	150 150	300 250	150 150	300 250	150 150	300 250	mA
		$f = 0^{(3)}$	IND.	S L			150 150	360 300	150 150	360 300	mA
ICC2	Dynamic Operating Current (All Ports Active)	$ \begin{array}{l} \overline{CE} = VIL \\ Outputs \ Disabled \\ f = fMAX^{(4)} \end{array} $	COM'L.	S L	240 210	370 325	225 195	350 305	210 180	335 290	mA
			IND.	S L			225 195	400 340	210 180	395 330	mA
ISB	Standby Current (All Ports - TTL Level Inputs)	II Ports - TTL Level $f = fMAX^{(4)}$	COM'L.	S L	70 60	95 80	60 50	85 70	40 35	75 60	mA
			IND.	S L			60 50	115 85	40 35	110 80	mA
ISB1	Full Standby Current (All Ports - All	Il Ports - All $\overline{CE} \ge Vcc - 0.2V$ MOS Level Inputs) $VIN \ge Vcc - 0.2V$ or	COM'L.	S L	1.5 0.3	15 1.5	1.5 0.3	15 1.5	1.5 0.3	15 1.5	mA
	CMOS Level Inputs)		IND.	S L			1.5 0.3	30 4.5	1.5 0.3	30 4.5	mA

3241 tbl 06

NOTES:

1. 'X' in part number indicates power rating (S or L).

2. Vcc = 5V, TA = +25°C and are not production tested.

3. f = 0 means no address or control lines change.

4. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tRc, and using "AC Test Conditions" of input levels of GND to 3V.

5. For the case of one port, divide the appropriate current above by four.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

			7054S		7054L		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
ILI	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, VIN = 0V to Vcc	_	10	_	5	μA
I lo	Output Leakage Current	\overline{CE} = VIH, VOUT = 0V to VCC	_	10	_	5	μA
Vol	Output Low Voltage	Iol = 4mA		0.4		0.4	V
Vон	Output High Voltage	Iон = -4mA	2.4	_	2.4		V

NOTE:

1. At Vcc \leq 2.0V input leakages are undefined.

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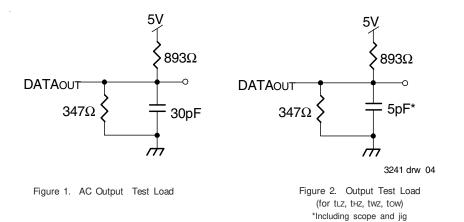


High-Speed 4K x 8 FourPort™ Static RAM

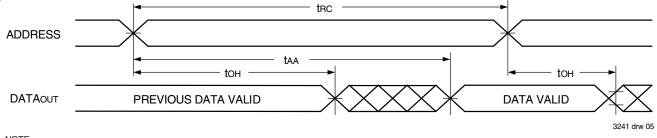
AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2

3241 tbl 08



Timing Waveform of Read Cycle No. 1, Any Port⁽¹⁾



NOTE: 1. R/ \overline{W} = VIH, \overline{OE} = VIL, and \overline{CE} = VIL.



AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽³⁾

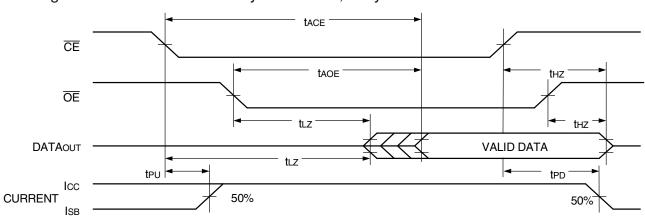
		7054X20 Com'l Only		7054X25 Com'l & Ind		7054X35 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE					-		-	
trc	Read Cycle Time	20		25		35		ns
taa	Address Access Time		20		25		35	ns
tace	Chip Enable Access Time		20	-	25		35	ns
taoe	Output Enable Access Time		10		15		25	ns
toн	Output Hold from Address Change	0		0		0		ns
t∟z	Output Low-Z Time ^(1,2)	5		5		5		ns
tнz	Output High-Z Time ^(1,2)		12		15		15	ns
tpu	Chip Enable to Power Up Time ⁽²⁾	0		0		0		ns
tpd	Chip Disable to Power Down Time ⁽²⁾		20		25		35	ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization but is not production tested.

3. 'X' in part number indicates power rating (S or L).



Timing Waveform of Read Cycle No. 2, Any $Port^{(1, 2)}$

3241 drw 06

3241 tbl 09

NOTES:

1. $R/\overline{W} = V_{IH}$ for Read Cycles.

2. Addresses valid prior to or coincident with $\overline{\text{CE}}$ transition LOW.



AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

		7054X20 Com'l Only		7054X25 Com'l & Ind		7054X35 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCL	E				-	-		
twc	Write Cycle Time	20		25		35		ns
tew	Chip Enable to End-of-Write	15		20		30		ns
taw	Address Valid to End-of-Write	15		20		30		ns
tas	Address Set-up Time	0		0		0		ns
twp	Write Pulse Width ⁽³⁾	15		20		30		ns
twR	Write Recovery Time	0		0		0		ns
tdw	Data Valid to End-of-Write	15		15		20		ns
tнz	Output High-Z Time ^(1,2)		15	_	15		15	ns
tdн	Data Hold Time	0		0		0		ns
twz	Write Enable to Output in High-Z ^(1,2)		12	_	15		15	ns
tow	Output Active from End-of-Write ^(1,2)	0		0		0		ns
twdd	Write Pulse to Data Delay ⁽⁴⁾		35		45		55	ns
tddd	Write Data Valid to Read Data Delay ⁽⁴⁾		30		35		45	ns

3241 tbl 10

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization but is not production tested.

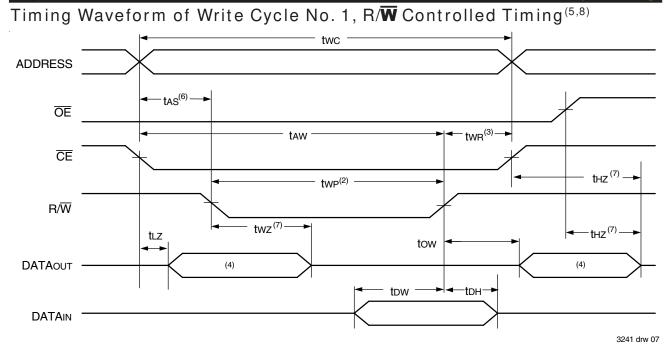
3. If OE = VL during a RW controlled write cycle, the write pulse width must be the larger of twP or (twz + tbw) to allow the I/O drivers to turn off data to be placed on the bus for the required tbw. If OE = VH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twP. Specified for OE = VH (refer to "Timing Waveform of Write Cycle", Note 8).

4. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read".

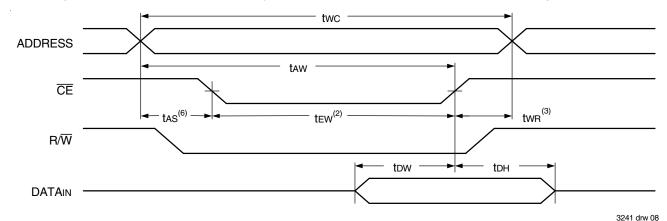
5. 'X' in part number indicates power rating.



Commercial Temperature Range



Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,5)

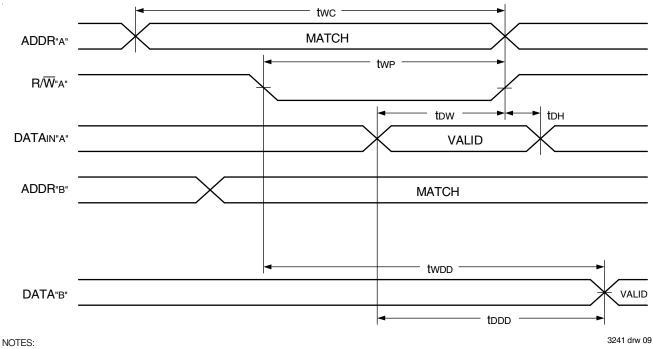


NOTES:

- 1. R/\overline{W} or $\overline{CE} = V_{IH}$ during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a \overline{CE} = VIL and a R/ \overline{W} = VIL.
- 3. two is measured from the earlier of \overline{CE} or $R/\overline{W} = V_{IH}$ to the end of write cycle.
- 4. During this period, the I/O pins are in the output state, and input signals must not be applied.
- 5. If the \overline{CE} LOW transition occurs simultaneously with or after the $R\overline{W} = VIL$ transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, $\overline{\text{CE}}$ or $\text{R}/\overline{\text{W}}$.
- 7. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed but is not production tested.
- 8. If OE = VIL during a R/W controlled write cycle, the write pulse width must be the larger of twP or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If OE = VIH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twP.







1. $\overline{OE} = V_{IL}$ for the reading ports.

2. All timing is the same for left and right ports. Port "A" may be either of the four ports and Port "B" is any other port.

Functional Description

The IDT7054 provides four ports with separate control, address, and I/O pins that permit independent access for reads or writes to any location in memory. These devices have an automatic power down feature controlled by \overline{CE} . The \overline{CE} controls on-chip power down circuitry that permits the respective port to go into standby mode when not selected ($\overline{CE} = VIH$). When a port is enabled, access to the entire memory array is permitted. Each port has its own Output Enable control (\overline{OE}). In the read mode, the port's \overline{OE} turns on the output drivers when set LOW. READ/WRITE conditions are illustrated in the table.

Table I - Read/Write Control

	Ar	ny Port ⁽¹)						
R∕ ₩	R/W CE OE D0-7		D0-7	Function					
х	Н	х	Z	Port Deselected: Power-Down					
х	х н х z		Z	CEP1=CEP2=CEP3=CEP4=V⊪ Power Down Mode ISB or ISB1					
L	L	х	DATAIN	Data on port written into memory ⁽²⁾					
Н	L	L	DATAOUT	Data in memory output on port					
х	х	н	Z	Outputs Disabled					

NOTES:

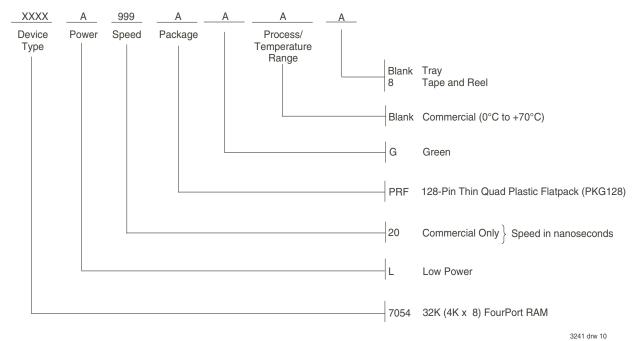
1. "H" = VIH, "L" = VIL, "X" = Don't Care, "Z "= High Impedance

2. For valid write operation, no more than one port can write to the same address location at the same time.



High-Speed 4K x 8 FourPort[™] Static RAM

Ordering Information



NOTE:

1. Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience.

Ordering Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
20	7054L20PRFG	PKG128	TQFP	С
	7054L20PRFG8	PKG128	TQFP	С

Datasheet Document History

01/18/99:	Initiated datasheet document history
	Converted to new format
	Cosmetic typographical corrections
	Added additional notes to pin configurations
06/04/99:	Changed drawing format
	Page 1 Corrected DSC number
09/01/99:	Removed Preliminary
11/10/99:	Replaced IDT logo
05/23/00:	Page 4 Increased storage temperature parameter
	Clarified TA parameter
	Page 5 DC Electrical parameters-changed wording from "open" to "disabled"
	Changed ±200mV to 0mV in notes
10/22/01:	Page 2 & 3 Added date revision for pin configurations
	Page 5, 7 & 8 Added Industrial temp to column heading for 25ns speed to DC & AC Electrical Characteristics
	Page 11 Added Industrial temp offering to 25ns ordering information
	Page 4, 5, 7 & 8 Removed Industrial temp footnote from all tables
	Page 6 Changed 5ns to 3ns in AC Test Conditions table
	Page 1 & 11 Replaced тм logo with ® logo
02/20/15:	Page 1 Added green availability to features
	Page 2 Removed IDT in reference to fabrication
	Page 2 2V battery backup for Low-power versions are no longer offered
	Page 2,3 & 10 The package code PK128-1 changed to PK128 to match standard package codes
	Page 10 Added Tape and Reel and Green to Ordering Information
	Pages 1-10 Removed all military data including the G108 pin configuration, changed table headings and ordering information
	to indicate that there is no longer a military offering for this 7054 device
07/02/18:	Product Discontinuation Notice - PDN# SP-17-02
	Last time buy expires June 15, 2018
07/11/19:	Pages 1 & 10 Deleted obsolete Commercial 25/35ns and Industrial 25ns speed grades
	Pages 1 & 10 Removed standard product offering and Industrial speed grade offering
	Pages 2 & 10 Updated package code PK128 to PKG128
	Page 10 Added Orderable Part Information
04/07/22:	Pages 1 - 12 Source file updated to reflect previous Corporate Marketing rebranding
	Page 2 Updated the package code



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